

International
IR Rectifier
 INSULATED GATE BIPOLAR TRANSISTOR

PD - 95645A

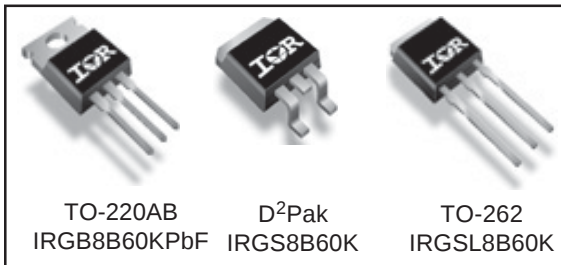
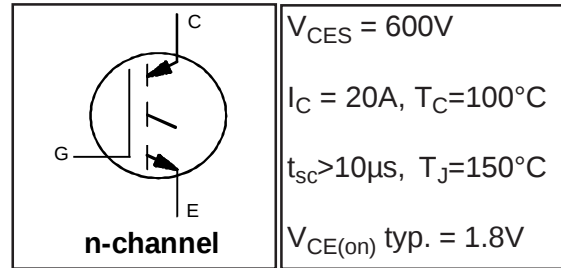
IRGB8B60KPbF
IRGS8B60KPbF
IRGSL8B60KPbF

Features

- Low VCE (on) Non Punch Through IGBT Technology.
- 10μs Short Circuit Capability.
- Square RBSOA.
- Positive VCE (on) Temperature Coefficient.
- Lead-Free.

Benefits

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	28	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	19	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	56	
I_{LM}	Clamped Inductive Load current ①	56	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	167	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	83	
T_J	Operating Junction and	-55 to +175	$^\circ C$
T_{STG}	Storage Temperature Range		
	Storage Temperature Range, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	—	—	0.90	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ②	—	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, Steady State)③	—	—	40	
	Weight	—	1.44	—	g

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 500\mu A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.57	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1mA (25^\circ\text{C}-150^\circ\text{C})$	
$V_{CE(on)}$	Collector-to-Emitter Voltage	—	1.8	2.2	V	$I_C = 8.0A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	5,6,7
		—	2.2	2.5		$I_C = 8.0A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	8,9,10
		—	2.3	2.6		$I_C = 8.0A, V_{GE} = 15V, T_J = 175^\circ\text{C}$	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$	8,9,10,
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-9.5	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 1mA (25^\circ\text{C}-125^\circ\text{C})$	11
gfe	Forward Transconductance	—	3.7	—	S	$V_{CE} = 50V, I_C = 8.0A, PW = 80\mu s$	
I_{CES}	Zero Gate Voltage Collector Current	—	1.0	150	μA	$V_{GE} = 0V, V_{CE} = 600V$	
		—	200	500		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
		—	800	1320		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q_g	Total Gate Charge (turn-on)	—	29	—	nC	$I_C = 8.0A$	17
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	3.7	—		$V_{CC} = 480V$	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	14	—		$V_{GE} = 15V$	
E_{on}	Turn-On Switching Loss	—	160	268	μJ	$I_C = 8.0A, V_{CC} = 400V$	CT4
E_{off}	Turn-Off Switching Loss	—	160	268		$V_{GE} = 15V, R_G = 50\Omega, L = 1.1mH$	
E_{tot}	Total Switching Loss	—	320	433		$T_J = 25^\circ\text{C} \text{ ④}$	
$t_{d(on)}$	Turn-On delay time	—	23	27	ns	$I_C = 8.0A, V_{CC} = 400V$	CT4
t_r	Rise time	—	22	26		$V_{GE} = 15V, R_G = 50\Omega, L = 1.1mH$	
$t_{d(off)}$	Turn-Off delay time	—	140	150		$T_J = 25^\circ\text{C}$	
t_f	Fall time	—	32	42			
E_{on}	Turn-On Switching Loss	—	220	330	μJ	$I_C = 8.0A, V_{CC} = 400V$	CT4
E_{off}	Turn-Off Switching Loss	—	270	381		$V_{GE} = 15V, R_G = 50\Omega, L = 1.1mH$	12,14
E_{tot}	Total Switching Loss	—	490	608		$T_J = 150^\circ\text{C} \text{ ④}$	WF1,WF2
$t_{d(on)}$	Turn-On delay time	—	22	27	ns	$I_C = 8.0A, V_{CC} = 400V$	13,15
t_r	Rise time	—	21	25		$V_{GE} = 15V, R_G = 50\Omega, L = 1.1mH$	CT4
$t_{d(off)}$	Turn-Off delay time	—	180	198		$T_J = 150^\circ\text{C}$	WF1
t_f	Fall time	—	40	56			WF2
C_{ies}	Input Capacitance	—	440	—	pF	$V_{GE} = 0V$	16
C_{oes}	Output Capacitance	—	38	—		$V_{CC} = 30V$	
C_{res}	Reverse Transfer Capacitance	—	16	—		$f = 1.0MHz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 150^\circ\text{C}, I_C = 34A, V_p = 600V$ $V_{CC}=500V, V_{GE} = +15V \text{ to } 0V, R_G = 50\Omega$	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	$T_J = 150^\circ\text{C}, V_p = 600V, R_G = 100\Omega$ $V_{CC}=360V, V_{GE} = +15V \text{ to } 0V$	CT3 WF3

Notes ① to ④ are on page 13.

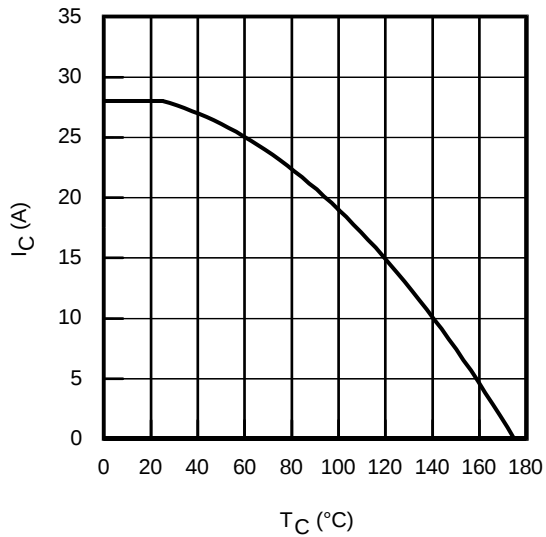


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

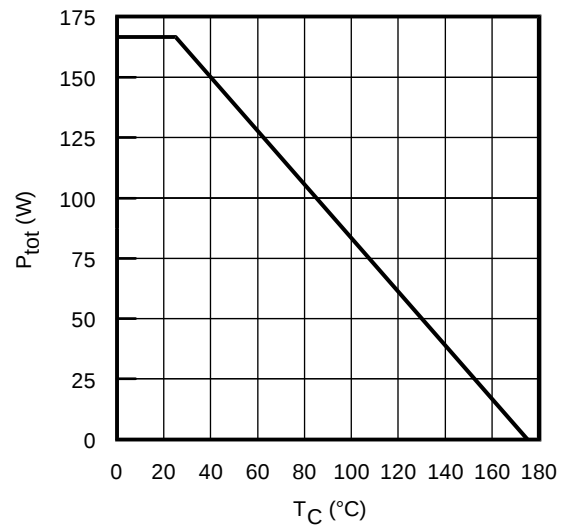


Fig. 2 - Power Dissipation vs. Case Temperature

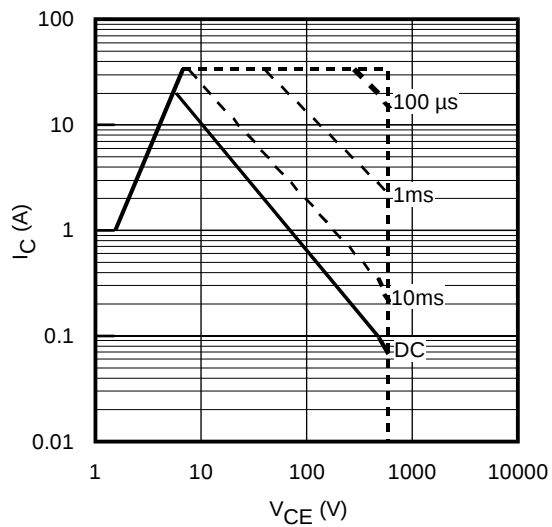


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$; $T_J \leq 150^\circ\text{C}$

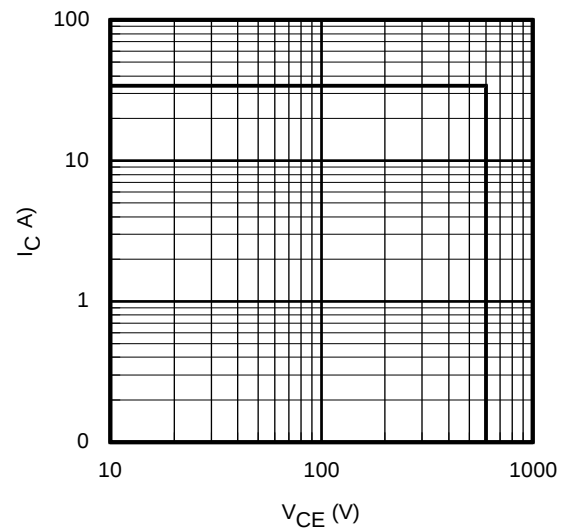


Fig. 4 - Reverse Bias SOA
 $T_J = 150^\circ\text{C}$; $V_{GE} = 15\text{V}$

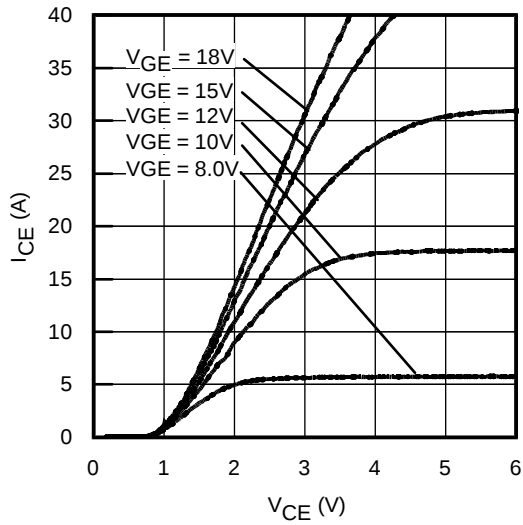


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

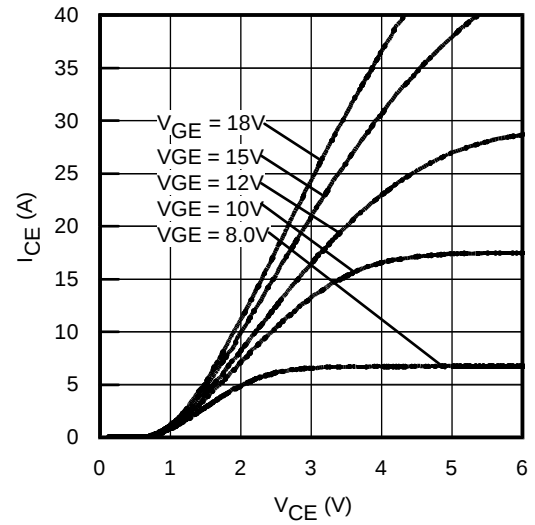


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

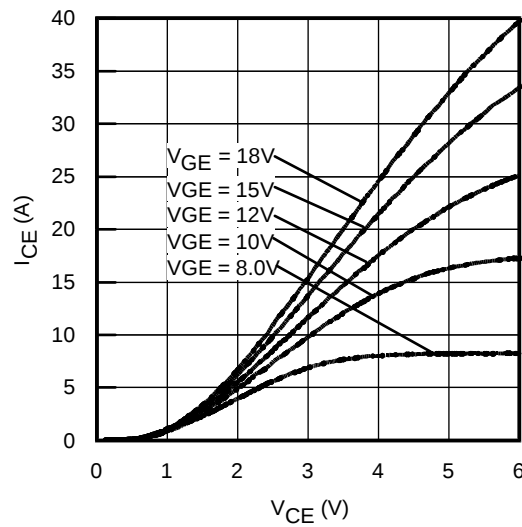


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 150^\circ\text{C}$; $t_p = 80\mu\text{s}$

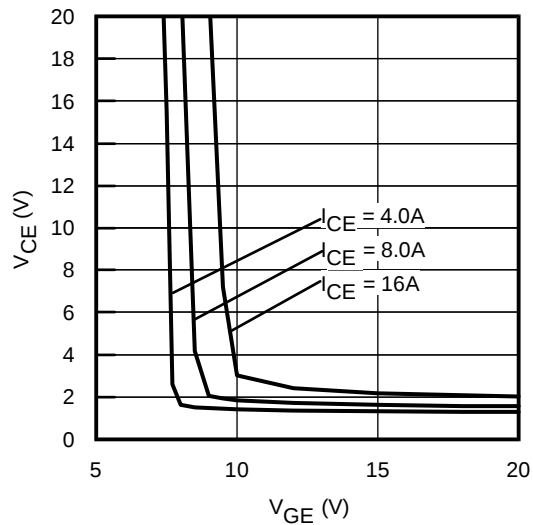


Fig. 8 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

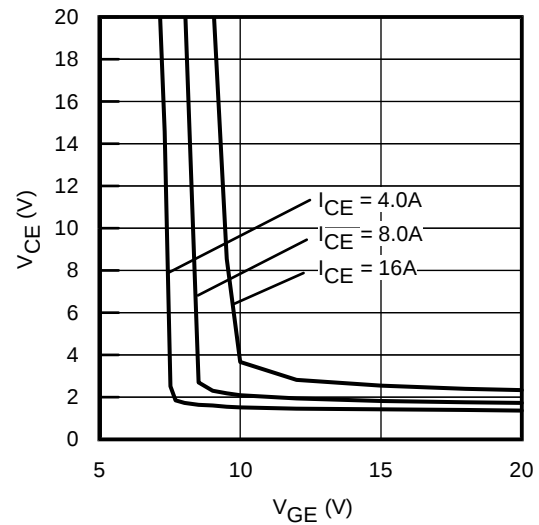


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

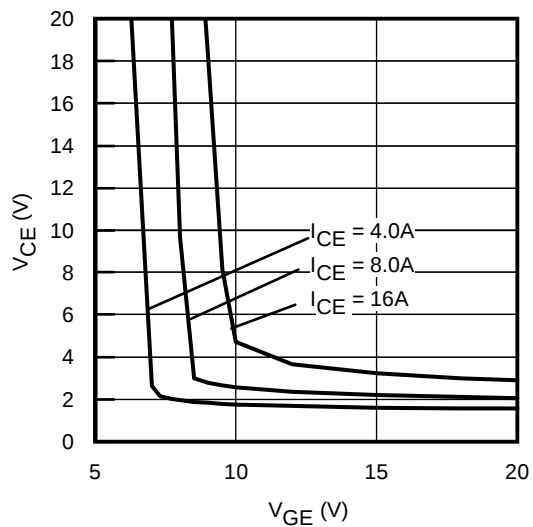


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^\circ\text{C}$

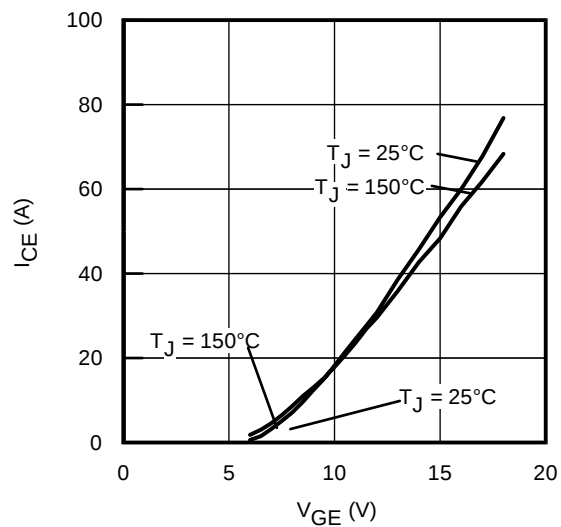


Fig. 11 - Typ. Transfer Characteristics
 $V_{CE} = 360\text{V}$; $t_p = 10\mu\text{s}$

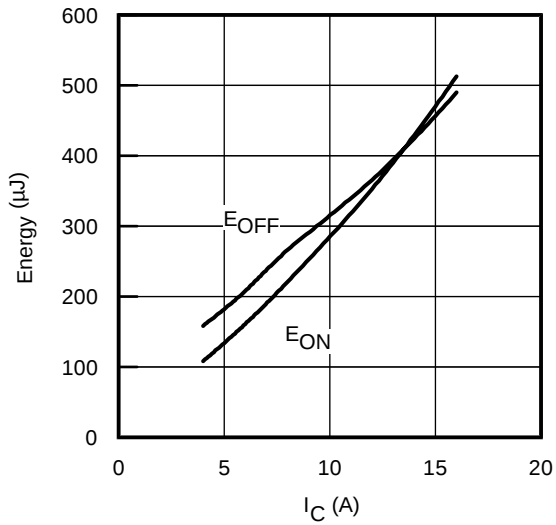


Fig. 12 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}$; $L=1.1\text{mH}$; $V_{CE}=400\text{V}$,
 $R_G=50\Omega$; $V_{GE}=15\text{V}$

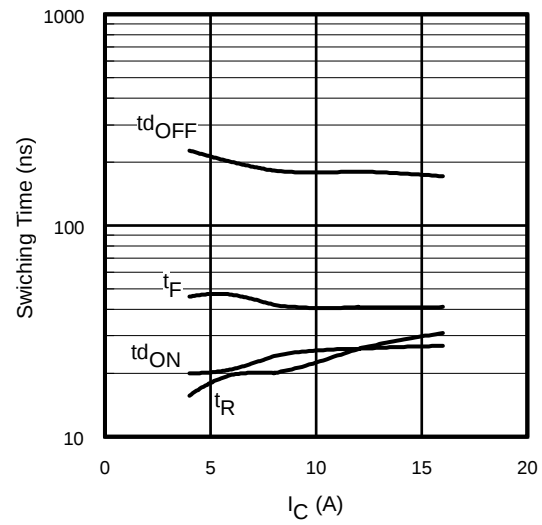


Fig. 13 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}$; $L=1.1\text{mH}$; $V_{CE}=400\text{V}$
 $R_G=50\Omega$; $V_{GE}=15\text{V}$

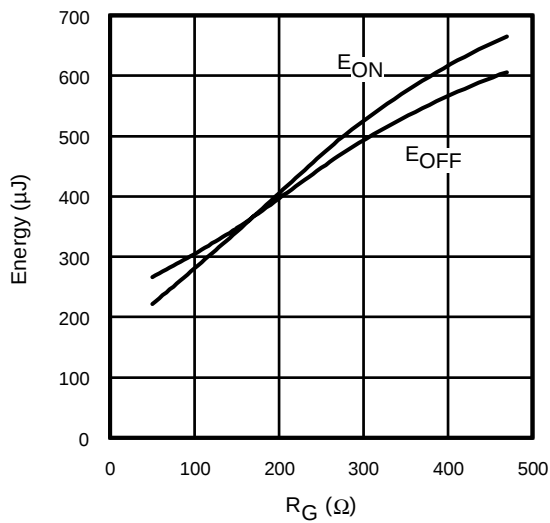


Fig. 14 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}$; $L=1.1\text{mH}$; $V_{CE}=400\text{V}$
 $I_{CE}=8.0\text{A}$; $V_{GE}=15\text{V}$

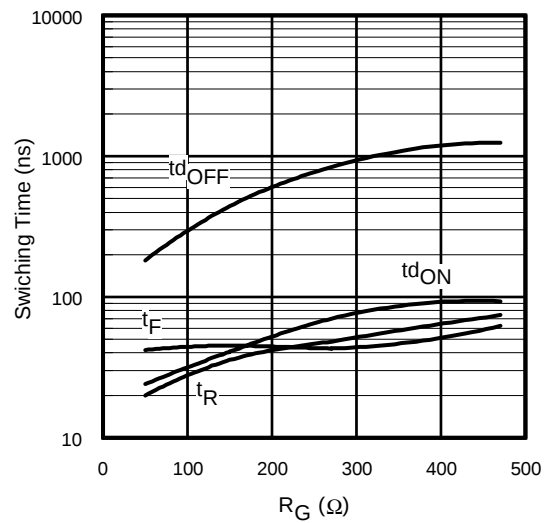


Fig. 15 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}$; $L=1.1\text{mH}$; $V_{CE}=400\text{V}$
 $I_{CE}=8.0\text{A}$; $V_{GE}=15\text{V}$

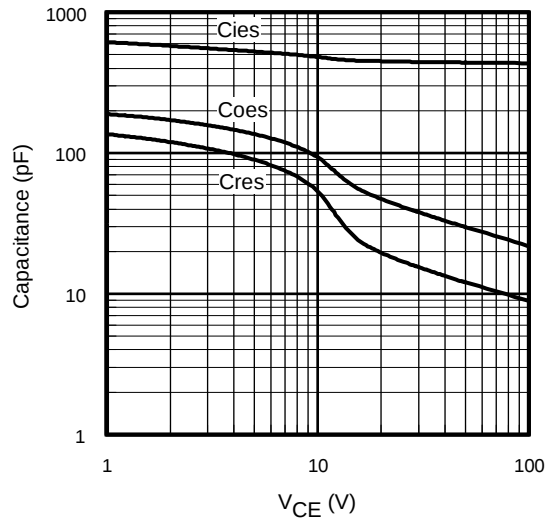


Fig. 16- Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

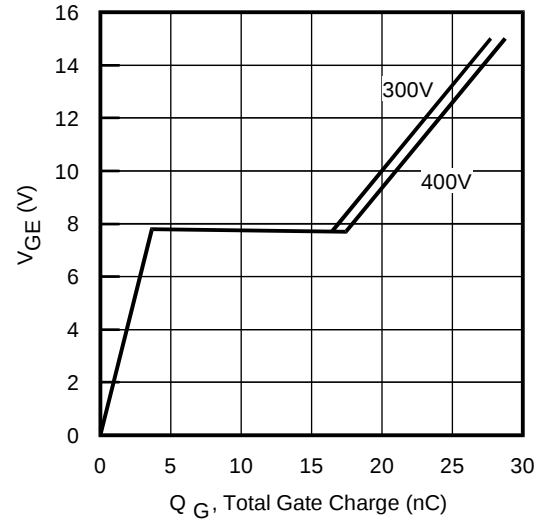


Fig. 17 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 8.0A$; $L = 600\mu H$

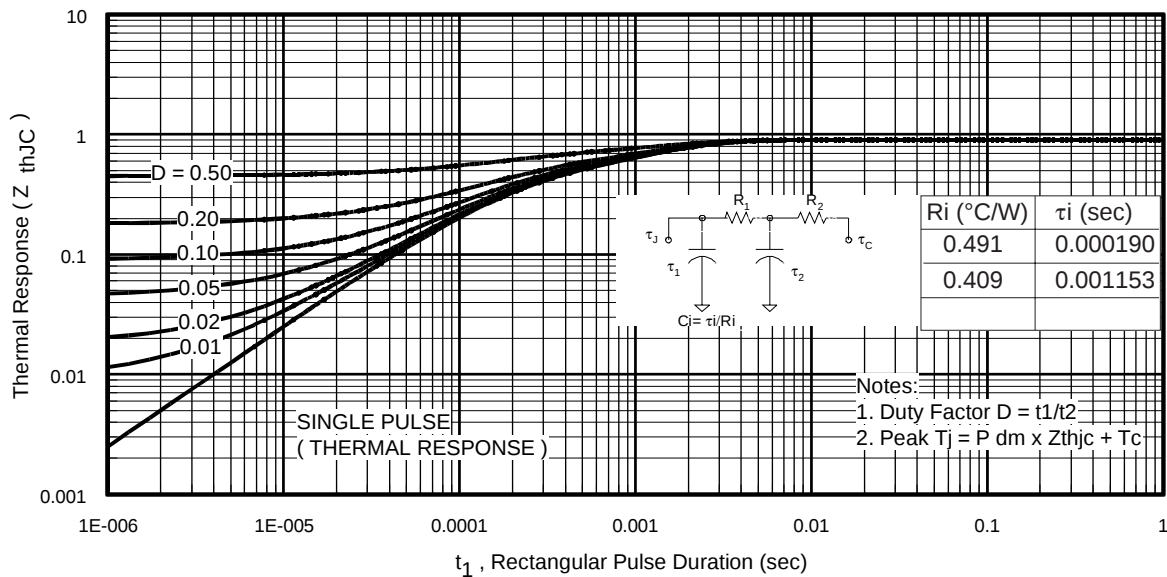


Fig 18. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

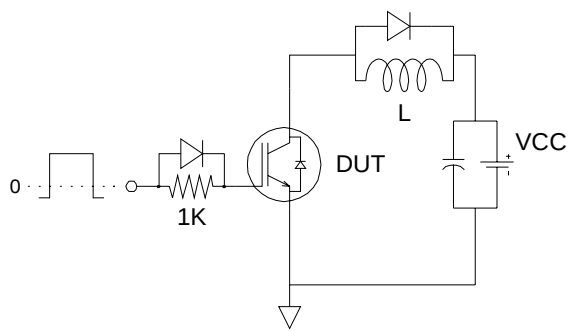


Fig.C.T.1 - Gate Charge Circuit (turn-off)

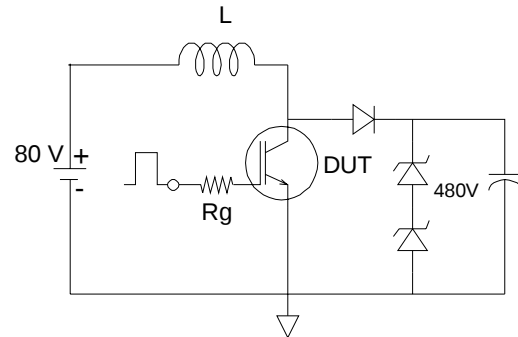


Fig.C.T.2 - RBSOA Circuit

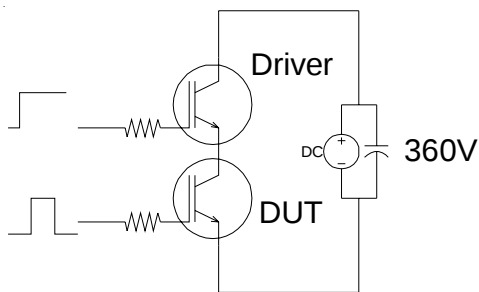


Fig.C.T.3 - S.C.SOA Circuit

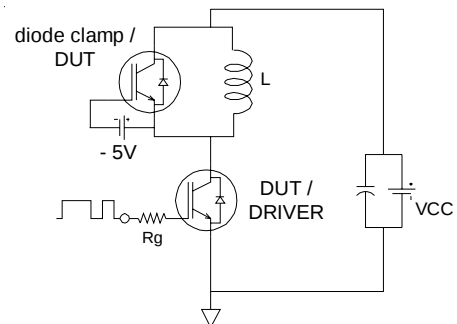


Fig.C.T.4 - Switching Loss Circuit

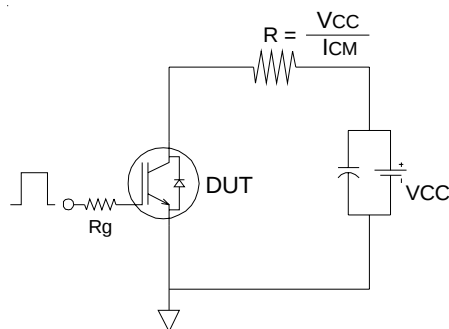


Fig.C.T.5 - Resistive Load Circuit

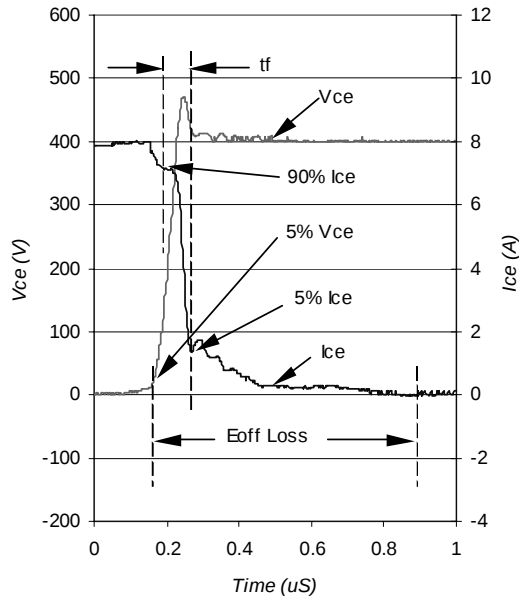


Fig. WF1- Typ. Turn-off Loss Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.4

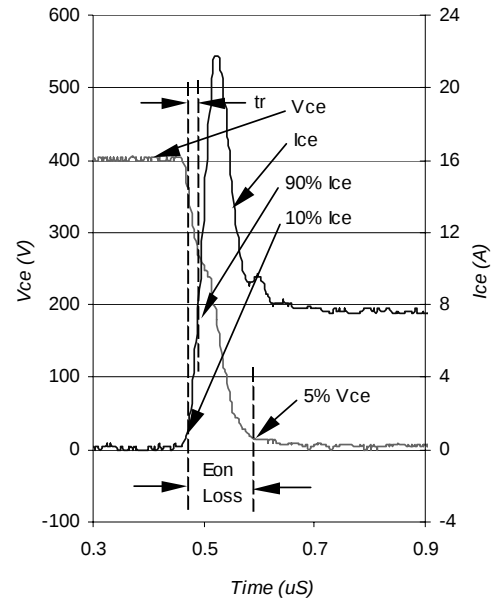


Fig. WF2- Typ. Turn-on Loss Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.4

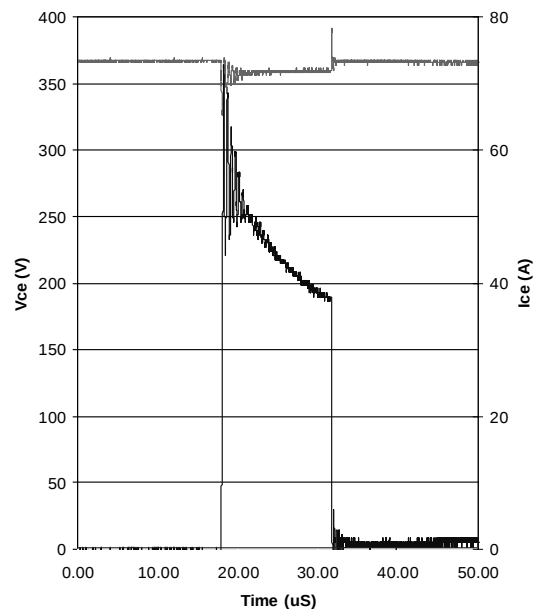


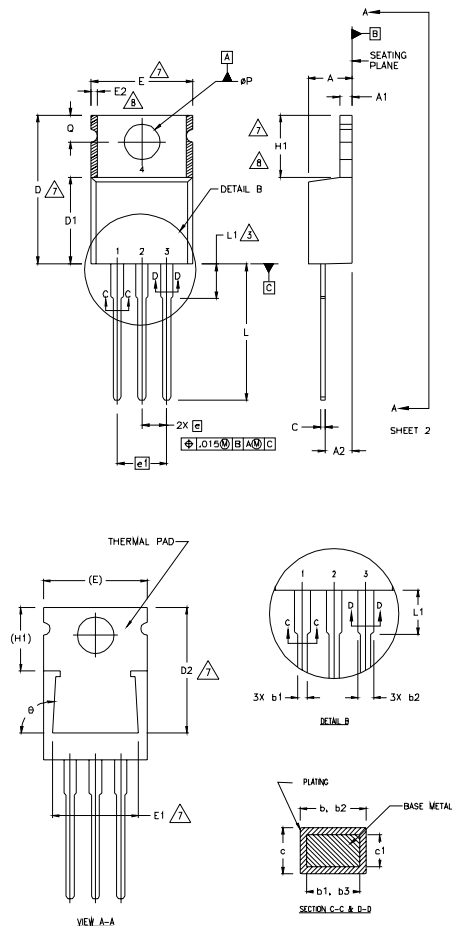
Fig. WF3- Typ. S.C Waveform
@ $T_C = 150^{\circ}\text{C}$ using Fig. CT.3

IRGB/S/SL8B60KPbF

International
IR Rectifier

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3. LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION : INCHES.
7. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8. DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFEET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs - GUPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

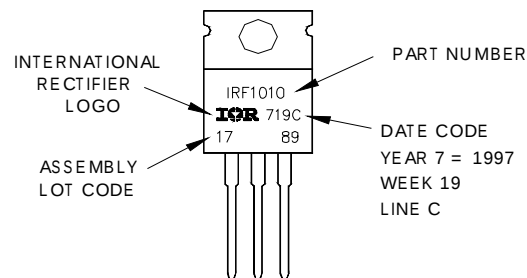
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	5
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	
b2	1.15	1.77	.045	.070	5
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	7
D2	12.19	12.88	.480	.507	
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		7,8
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	3
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	3
Ø	90°-93°		90°-93°		

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010

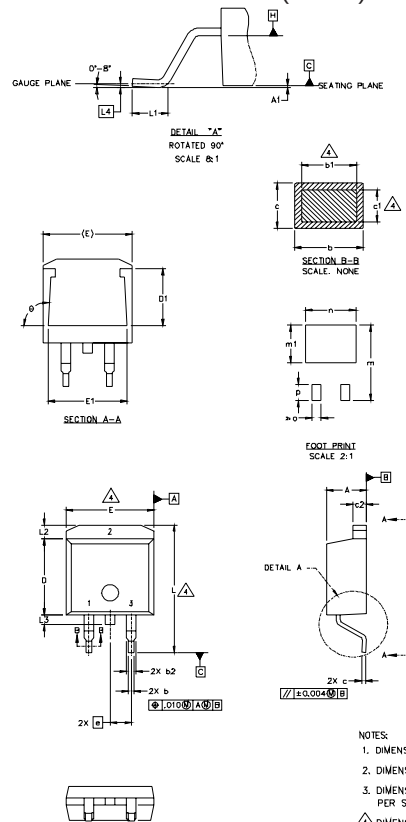
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25	BSC	.010	BSC	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

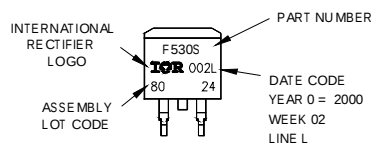
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

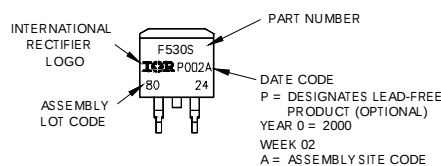
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

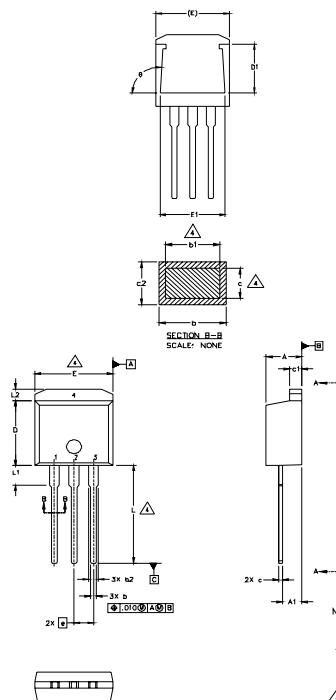


IRGB/S/SL8B60KPbF

International
IR Rectifier

TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	3
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

- 1. - GATE
- 2. - DRAIN
- 3. - SOURCE
- 4. - DRAIN

IGBT

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

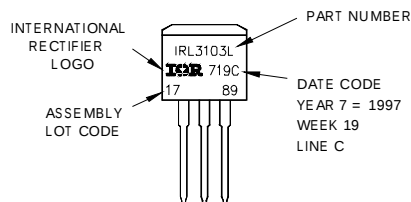
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH

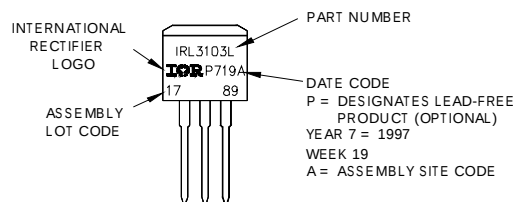
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

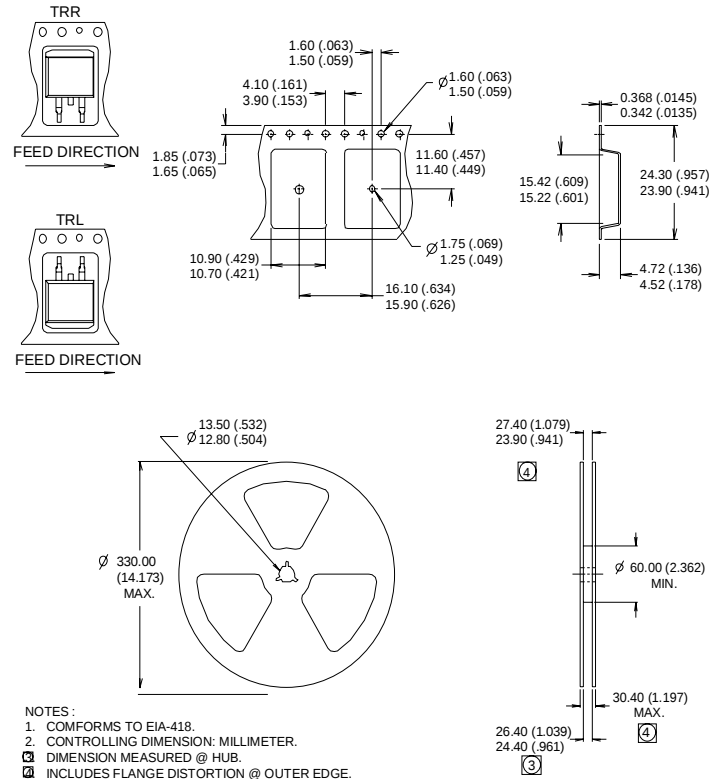


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Notes:

- ① $V_{CC} = 80\% (V_{CES})$, $V_{GE} = 15V$, $L = 100\mu H$, $R_G = 50\Omega$.
- ② This is only applied to TO-220AB package.
- ③ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.
- ④ Energy losses include "tail" and diode reverse recovery, using Diode HF03D060ACE.

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.